

What is claimed is:

1. A method of analyzing plasma, said method comprising: igniting the plasma using an RF signal; monitoring the RF signal as the RF signal is used to ignite the plasma; calculating a value based on the RF signal; integrating the calculated value over a period of time to determine effects of a pre-determined parameter.
2. The method as recited in claim 1, further comprising using an RF signal monitor to monitor the RF signal, calculate the value, and integrate the calculated value.
3. The method as recited in claim 1, further comprising using the integrated value to calculate etch rate.
4. The method as recited in claim 1, further comprising using the integrated value to calculate at least one etch chamber condition.
5. The method as recited in claim 1, further comprising using the integrated value to calculate at least one of pressure, flow and gap

spacing associated with an etch chamber.

6. The method as recited in claim 1, further comprising integrating a plurality of parts of the RF signal.